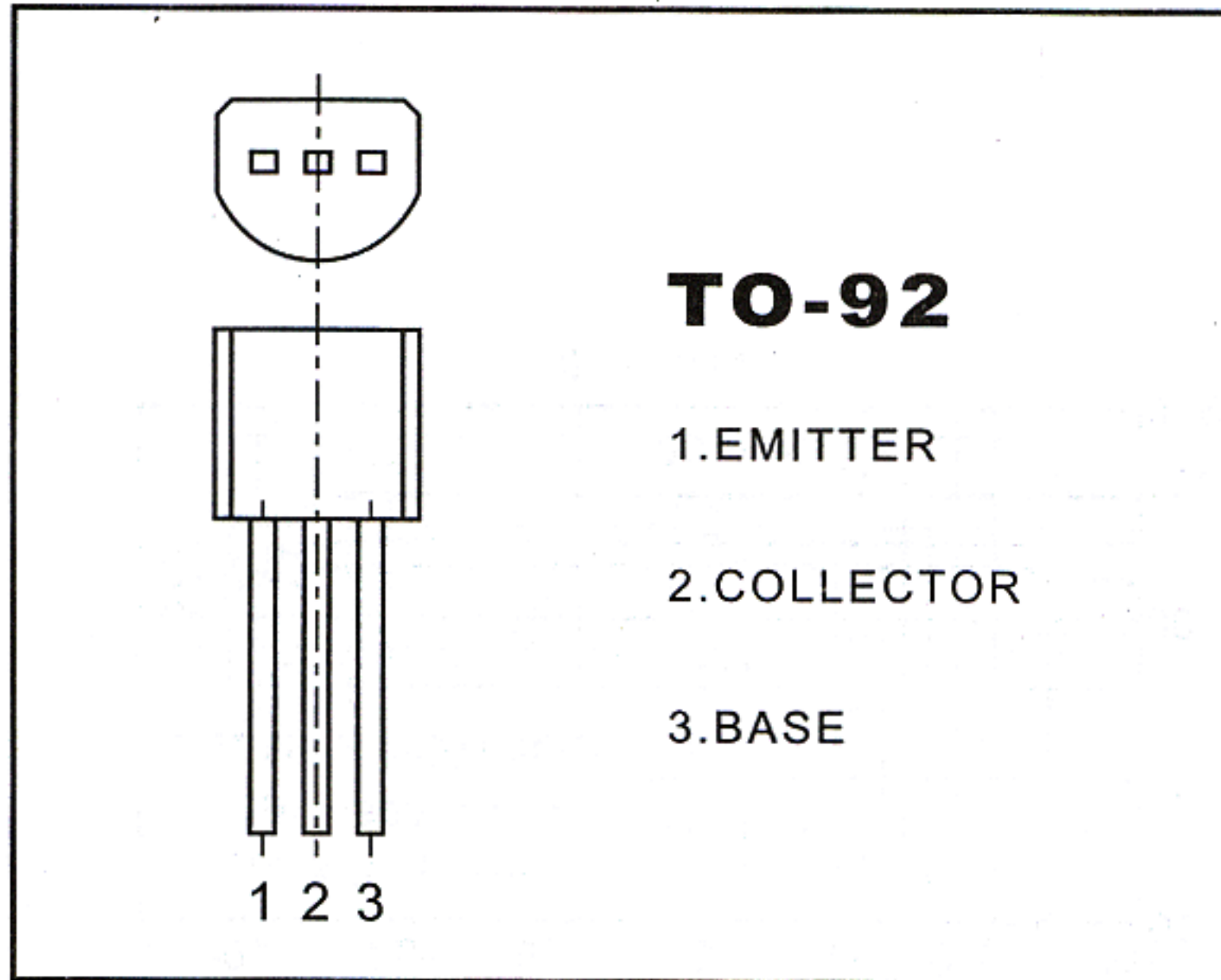


A1015 TRANSISTOR(PNP)



FEATURES

Power dissipation

P_{CM} : 0.4W ($T_{amb}=25^{\circ}C$)

Collector current

I_{CM} : -0.15A

Collector-base voltage

$V_{(BR)CBO}$: -50 V

Operating and storage junction temperature range

T_J, T_{stg} : $-55^{\circ}C$ to $+150^{\circ}C$

ELECTRICAL CHARACTERISTICS

($T_{amb}=25^{\circ}C$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C = -100 \mu A, I_E = 0$	-50		V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = -0.1 mA, I_B = 0$	-50		V
Collector cut-off current	I_{CBO}	$V_{CB} = -50 V, I_E = 0$		-0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB} = -5 V, I_C = 0$		-0.1	μA
DC current gain	h_{FE}	$V_{CE} = -6 V, I_C = -2 mA$	70	400	
Collector-emitter saturation voltage	V_{CEsat}	$I_C = -100 mA, I_B = -10 mA$		-0.3	V
Base-emitter saturation voltage	V_{BEsat}	$I_C = -100 mA, I_B = -10 mA$		-1.1	V
Base-emitter voltage	V_{BE}	$I_E = -310 mA$		-1.45	V
Transition frequency	f_T	$V_{CE} = -10 V, I_C = -1 mA$ $f = 30 MHz$	80		MHz

CLASSIFICATION OF h_{FE}

Rank	O	Y	GR
Range	70-140	120-240	200-400

